

NX3V1T66

Low-voltage analog switch

Rev. 01 — 27 March 2008

Product data sheet

1. General description

The NX3V1T66 provides one single-pole, single-throw analog switch function. It has two input/output terminals (Y and Z) and an active HIGH enable input pin (E). When pin E is LOW, the analog switch is turned off.

A low input voltage threshold allows pin E to be driven by lower level logic signals without a significant increase in supply current I_{CC} . This makes it possible for the NX3V1T66 to switch 3.6 V signals with a 1.8 V digital controller, eliminating the need for logic level translation.

The NX3V1T66 allows signals with amplitude up to V_{CC} to be transmitted from Y to Z or from Z to Y. Its ultra-low ON resistance (0.3 Ω) and flatness (0.1 Ω) ensures minimal attenuation and distortion of transmitted signals.

2. Features

- Wide supply voltage range from 1.4 V to 3.6 V
- Very low ON resistance (peak):
 - ◆ 0.8 Ω (typical) at $V_{CC} = 1.4$ V
 - ◆ 0.5 Ω (typical) at $V_{CC} = 1.65$ V
 - ◆ 0.3 Ω (typical) at $V_{CC} = 2.3$ V
 - ◆ 0.25 Ω (typical) at $V_{CC} = 2.7$ V
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114E Class 3A exceeds 7500 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
- CMOS low-power consumption
- Latch-up performance exceeds 100 mA per JESD 78 Class II Level A
- Enable input accepts voltages above supply voltage
- 1.8 V control logic at $V_{CC} = 3.6$ V
- High current handling capability (500 mA continuous current under 3.3 V supply)
- Specified from -40 °C to $+85$ °C and from -40 °C to $+125$ °C

3. Applications

- Cell phone
- PDA
- Portable media player

4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
NX3V1T66GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886

5. Marking

Table 2. Marking

Type number	Marking code
NX3V1T66GM	dO

6. Functional diagram

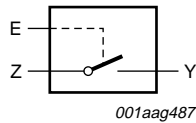


Fig 1. Logic symbol

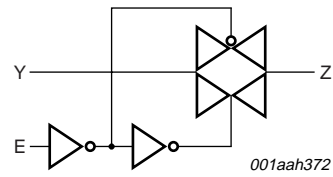


Fig 2. Logic diagram

7. Pinning information

7.1 Pinning

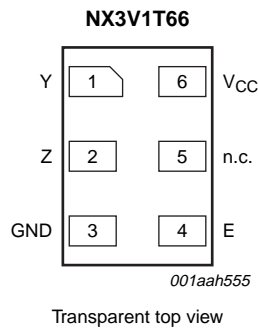


Fig 3. Pin configuration SOT886 (XSON6)

7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
Y	1	independent Y input or output
Z	2	independent Z input or output
GND	3	ground (0 V)
E	4	enable input (active HIGH)
n.c.	5	not connected
V _{CC}	6	supply voltage

8. Functional description

Table 4. Function table^[1]

Input E	Switch
L	OFF-state
H	ON-state

- [1] H = HIGH voltage level;
L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
V _I	input voltage	enable input E	^[1] -0.5	+4.6	V
V _{SW}	switch voltage		^[2] -0.5	V _{CC} + 0.5	V
I _{IK}	input clamping current	V _I < -0.5 V	-50	-	mA
I _{SK}	switch clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±50	mA
I _{SW}	switch current	V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; source or sink current	-	±500	mA
		V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; pulsed at 1 ms duration, < 10 % duty cycle; peak current	-	±750	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[3] -	250	mW

- [1] The minimum input voltage rating may be exceeded if the input current rating is observed.
 [2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.
 [3] For XSON6 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.4	3.6	V
V_I	input voltage	enable input E	0	3.6	V
V_{SW}	switch voltage		[1] 0	V_{CC}	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.4\text{ V to }3.6\text{ V}$	[2] -	200	ns/V

[1] To avoid sinking GND current from of terminal Z when switch current flows in terminal Y, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current will flow from terminal Y. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	0.9	-	-	0.9	-	-	V
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	0.9	-	-	0.9	-	-	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.1	-	-	1.1	-	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	1.3	-	-	1.3	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	-	-	0.3	-	0.3	0.3	V
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	-	-	0.4	-	0.4	0.3	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	-	-	0.4	-	0.4	0.4	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	0.5	-	0.5	0.5	V
I_I	input leakage current	enable input E; $V_I = \text{GND to }3.6\text{ V}$; $V_{CC} = 1.4\text{ V to }3.6\text{ V}$	-	-	-	-	±0.5	±1	µA
$I_{S(OFF)}$	OFF-state leakage current	Y port; see Figure 4 ; $V_{CC} = 1.4\text{ V to }3.6\text{ V}$;	-	-	±5	-	±50	±500	nA
$I_{S(ON)}$	ON-state leakage current	Z port; see Figure 5 ; $V_{CC} = 1.4\text{ V to }3.6\text{ V}$;	-	-	±5	-	±50	±500	nA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $V_{CC} = 3.6\text{ V}$; $V_{SW} = \text{GND or }V_{CC}$; $I_O = 0\text{ A}$	-	-	±100	-	690	6000	nA
ΔI_{CC}	additional supply current	$V_I = 2.6\text{ V}$; $V_{CC} = 3.6\text{ V}$; $V_{SW} = \text{GND or }V_{CC}$	-	0.35	0.7	-	1	1	µA
		$V_I = 1.8\text{ V}$; $V_{CC} = 3.6\text{ V}$; $V_{SW} = \text{GND or }V_{CC}$	-	2.5	4	-	5	5	µA
		$V_I = 1.8\text{ V}$; $V_{CC} = 2.5\text{ V}$; $V_{SW} = \text{GND or }V_{CC}$	-	50	200	-	300	500	nA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
C_I	input capacitance		-	1.0	-	-	-	-	pF
$C_{S(OFF)}$	OFF-state capacitance		-	70	-	-	-	-	pF
$C_{S(ON)}$	ON-state capacitance		-	205	-	-	-	-	pF

11.1 Test circuits

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$V_I = 0.3 \text{ V or } V_{CC} - 0.3 \text{ V}; V_O = V_{CC} - 0.3 \text{ V or } 0.3 \text{ V}.$

Fig 4. Test circuit for measuring OFF-state leakage current

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$V_I = 0.3 \text{ V or } V_{CC} - 0.3 \text{ V}; V_O = \text{open circuit}.$

Fig 5. Test circuit for measuring ON-state leakage current

11.2 ON resistance

Table 8. Resistance R_{ON}

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for graphs see [Figure 7](#) to [Figure 12](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit	
			Min	Typ ^[1]	Max	Min	Max		
$R_{ON(peak)}$	ON resistance (peak)	$V_I = \text{GND to } V_{CC}; I_{SW} = 100 \text{ mA};$ see Figure 6	$V_{CC} = 1.4 \text{ V}$	-	0.8	1.9	-	2.1	Ω
			$V_{CC} = 1.65 \text{ V}$	-	0.5	0.8	-	0.9	Ω
			$V_{CC} = 2.3 \text{ V}$	-	0.3	0.5	-	0.6	Ω
			$V_{CC} = 2.7 \text{ V}$	-	0.25	0.45	-	0.5	Ω
$R_{ON(flat)}$	ON resistance (flatness)	$V_I = \text{GND to } V_{CC}; I_{SW} = 100 \text{ mA}$ [2]	$V_{CC} = 1.4 \text{ V}$	-	0.5	1.7	-	1.8	Ω
			$V_{CC} = 1.65 \text{ V}$	-	0.25	0.6	-	0.7	Ω
			$V_{CC} = 2.3 \text{ V}$	-	0.1	0.2	-	0.2	Ω
			$V_{CC} = 2.7 \text{ V}$	-	0.1	0.2	-	0.2	Ω

[1] Typical values are measured at $T_{amb} = 25 \text{ }^\circ\text{C}$.

[2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

11.3 ON resistance test circuit and graphs

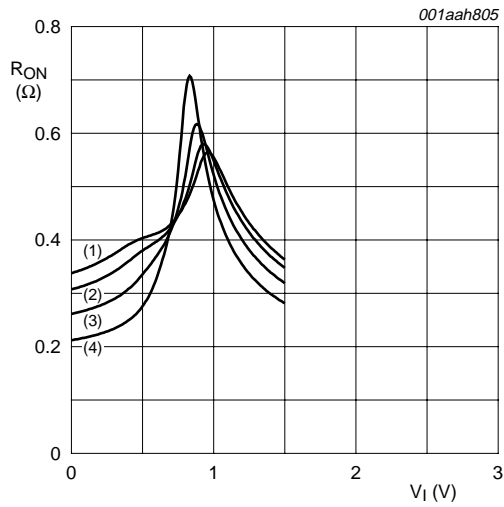
$R_{ON} = V_{SW} / I_{SW}$.

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Fig 6. Test circuit for measuring ON resistance

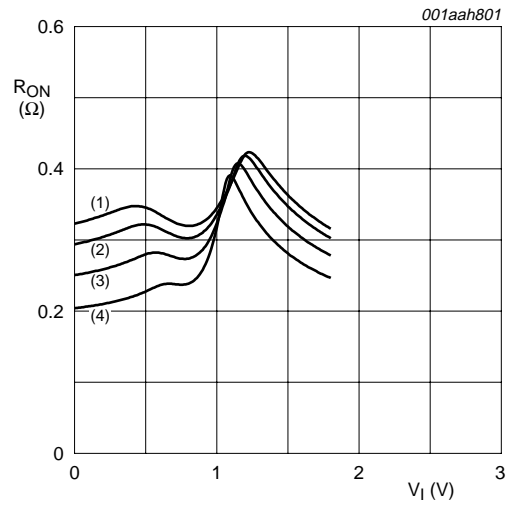
Fig 7. Typical ON resistance as a function of input voltage

(1) $V_{CC} = 1.5 \text{ V}$.
 (2) $V_{CC} = 1.8 \text{ V}$.
 (3) $V_{CC} = 2.5 \text{ V}$.
 (4) $V_{CC} = 2.7 \text{ V}$.
 (5) $V_{CC} = 3.3 \text{ V}$.
 Measured at $T_{amb} = 25 \text{ }^\circ\text{C}$.



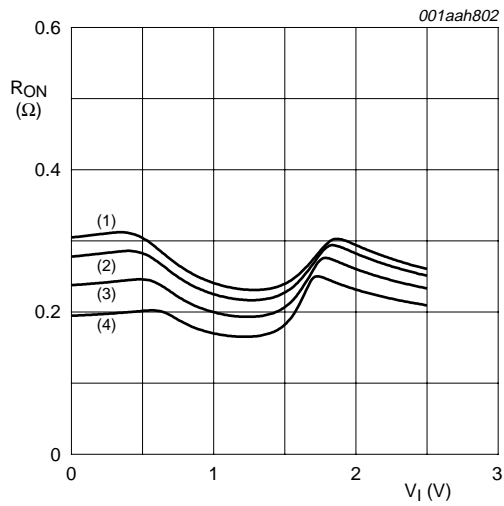
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 8. ON resistance as a function of input voltage;
 $V_{CC} = 1.5\text{ V}$



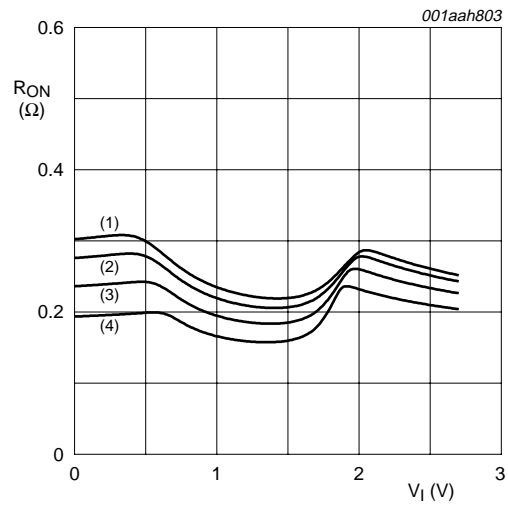
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 9. ON resistance as a function of input voltage;
 $V_{CC} = 1.8\text{ V}$



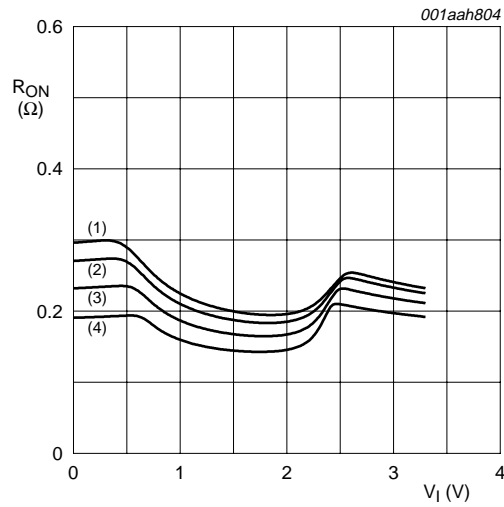
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 10. ON resistance as a function of input voltage;
 $V_{CC} = 2.5\text{ V}$



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 11. ON resistance as a function of input voltage;
 $V_{CC} = 2.7\text{ V}$



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}$.

Fig 12. ON resistance as a function of input voltage; $V_{CC} = 3.3\text{ V}$

12. Dynamic characteristics

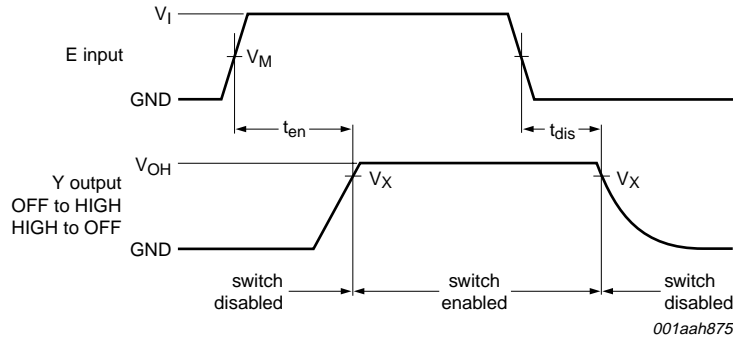
Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit [Figure 14](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t_{en}	enable time	E to Y; see Figure 13							
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	-	35	49	-	53	57	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	-	28	40	-	43	48	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	-	20	30	-	32	35	ns
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	18	28	-	30	32	ns
t_{dis}	disable time	E to Y; see Figure 13							
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	-	32	70	-	80	90	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	-	23	55	-	60	65	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	-	14	25	-	30	35	ns
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	11	20	-	25	30	ns

[1] Typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$ and $V_{CC} = 1.5\text{ V, }1.8\text{ V, }2.5\text{ V}$ and 3.3 V respectively.

12.1 Waveform and test circuits

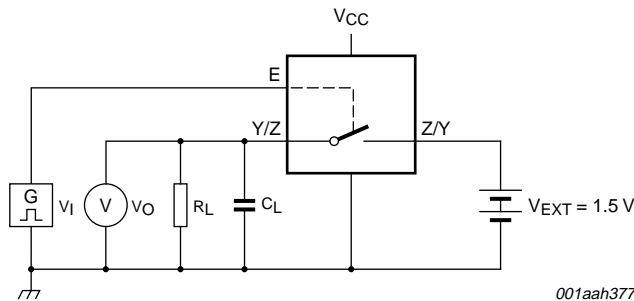


Measurement points are given in [Table 10](#).
 Logic level: V_{OH} is the typical output voltage that occurs with the output load.

Fig 13. Enable and disable times

Table 10. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_X
1.4 V to 3.6 V	$0.5V_{CC}$	$0.9V_{OH}$



Test data is given in [Table 11](#).
 Definitions test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.
 V_{EXT} = External voltage for measuring switching times.

Fig 14. Load circuit for switching times

Table 11. Test data

Supply voltage	Input	Load
V_{CC}	V_I	C_L R_L
1.4 V to 3.6 V	V_{CC}	≤ 2.5 ns 35 pF 50 Ω

12.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $V_I = \text{GND}$ or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5 \text{ ns}$; $T_{amb} = 25^\circ\text{C}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	$f_i = 20 \text{ Hz to } 20 \text{ kHz}$; $R_L = 32 \Omega$; see Figure 15	[1]			
		$V_{CC} = 1.4 \text{ V}$; $V_I = 1 \text{ V (p-p)}$	-	0.05	-	%
		$V_{CC} = 1.65 \text{ V}$; $V_I = 1.2 \text{ V (p-p)}$	-	0.03	-	%
		$V_{CC} = 2.3 \text{ V}$; $V_I = 1.5 \text{ V (p-p)}$	-	0.01	-	%
		$V_{CC} = 2.7 \text{ V}$; $V_I = 2 \text{ V (p-p)}$	-	0.01	-	%
$f_{(-3\text{dB})}$	-3 dB frequency response	$R_L = 50 \Omega$; see Figure 16	[1]			
		$V_{CC} = 1.4 \text{ V to } 3.6 \text{ V}$	-	25	-	MHz
α_{iso}	isolation (OFF-state)	$f_i = 100 \text{ kHz}$; $R_L = 50 \Omega$; see Figure 17	[1]			
		$V_{CC} = 1.4 \text{ V to } 3.6 \text{ V}$	-	-90	-	dB
V_{ct}	crosstalk voltage	between digital inputs and switch; $f_i = 1 \text{ MHz}$; $C_L = 50 \text{ pF}$; $R_L = 50 \Omega$; see Figure 18				
		$V_{CC} = 1.4 \text{ V to } 3.6 \text{ V}$	-	0.32	-	V
Q_{inj}	charge injection	$f_i = 1 \text{ MHz}$; $C_L = 0.1 \text{ nF}$; $R_L = 1 \text{ M}\Omega$; $V_{\text{gen}} = 0 \text{ V}$; $R_{\text{gen}} = 0 \Omega$; see Figure 19				
		$V_{CC} = 1.5 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 1.8 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 2.5 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 3.3 \text{ V}$	-	6.5	-	pC

[1] f_i is biased at $0.5V_{CC}$.

12.3 Test circuits

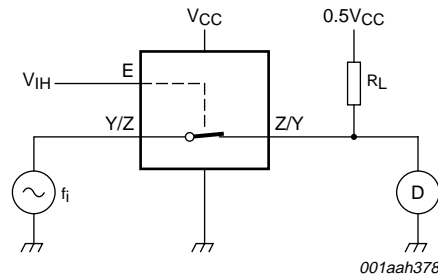
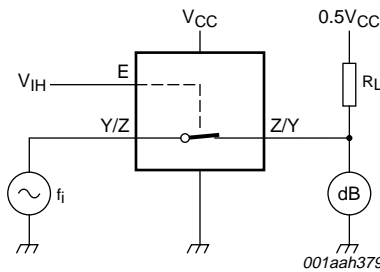
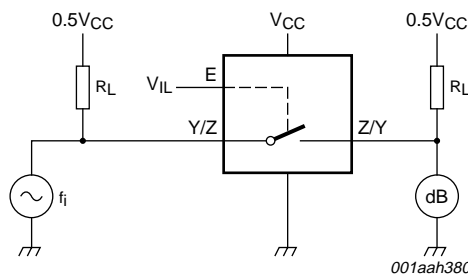


Fig 15. Test circuit for measuring total harmonic distortion



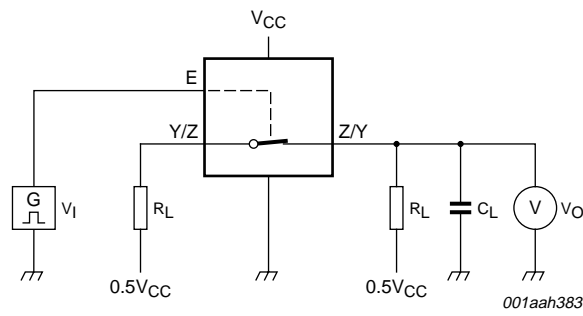
Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads -3 dB.

Fig 16. Test circuit for measuring the frequency response when channel is in ON-state

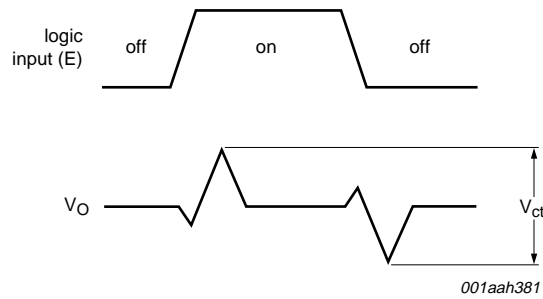


Adjust f_i voltage to obtain 0 dBm level at input.

Fig 17. Test circuit for measuring isolation (OFF-state)

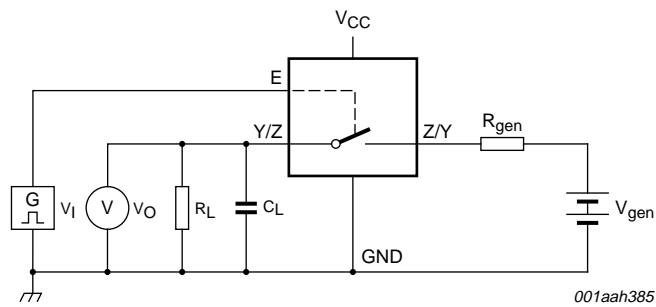


a. Test circuit

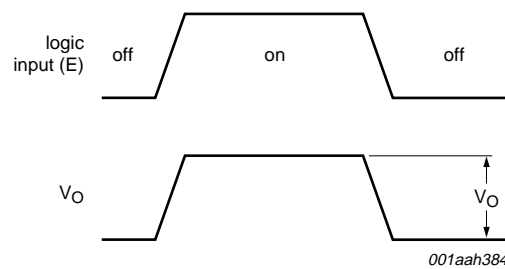


b. Input and output pulse definitions

Fig 18. Test circuit for measuring crosstalk voltage between digital inputs and switch



a. Test circuit



b. Input and output pulse definitions

Definition: $Q_{inj} = \Delta V_O \times C_L$.

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

V_{gen} = generator voltage.

Fig 19. Test circuit for measuring charge injection

13. Package outline

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

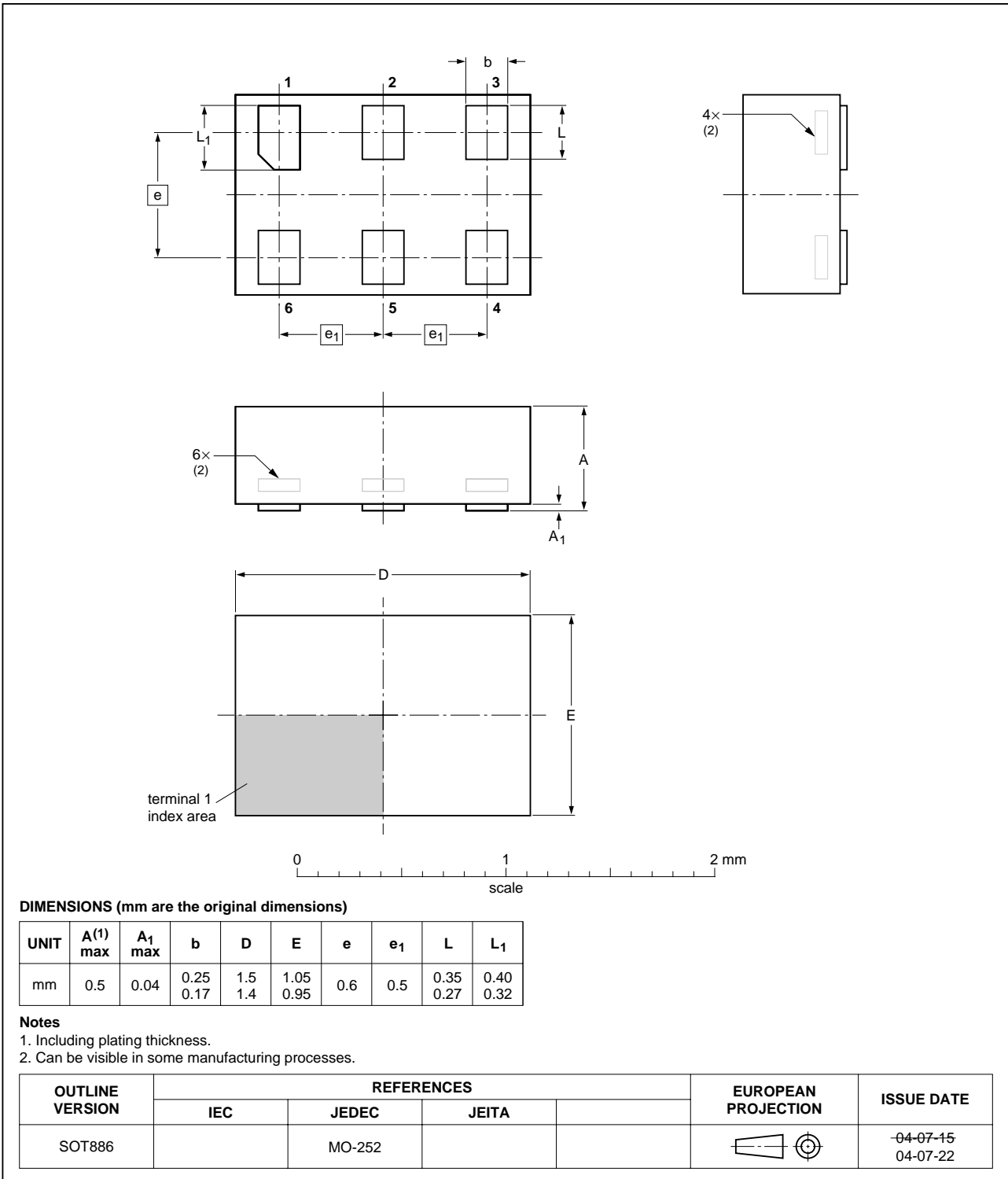


Fig 20. Package outline SOT886 (XSON6)

14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3V1T66_1	20080327	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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18. Contents

1 General description 1

2 Features 1

3 Applications 1

4 Ordering information 2

5 Marking 2

6 Functional diagram 2

7 Pinning information 2

7.1 Pinning 2

7.2 Pin description 3

8 Functional description 3

9 Limiting values 3

10 Recommended operating conditions 4

11 Static characteristics 4

11.1 Test circuits 5

11.2 ON resistance 6

11.3 ON resistance test circuit and graphs 6

12 Dynamic characteristics 8

12.1 Waveform and test circuits 9

12.2 Additional dynamic characteristics 10

12.3 Test circuits 11

13 Package outline 14

14 Abbreviations 15

15 Revision history 15

16 Legal information 16

16.1 Data sheet status 16

16.2 Definitions 16

16.3 Disclaimers 16

16.4 Trademarks 16

17 Contact information 16

18 Contents 17

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